

IN THE CLAIMS

Cancel claims 1-11.

12. (currently amended) A method of constructing a solid state device comprising the steps of:

    forming a first layer including an active region and a termination region using a first mask; and

    forming at least a second layer including an active region and a termination region having a lateral dimension and a vertical dimension using a second mask, the first and second mask being different for the portions portions corresponding to the termination region.—; and

providing a charge density in said termination region that decreases in both said lateral dimension and said vertical dimension as a direct function of a distance from said active region.

13. (Original) The method of claim 12 wherein the step of forming at least a second layer includes using a second mask that is substantially identical to the first mask in the portion corresponding to the active region.

14. (currently amended) A method of forming a termination region for a solid state device, the termination region

having a width lateral dimension and a depth vertical dimension, the method comprising the steps of:

- (a) doping the termination region in varying charge concentrations along the width lateral dimension; and
- (b) doping the termination region in varying charge concentrations along the depth vertical dimension.

15. (currently amended) The method of claim 14 wherein the step (a) of doping includes placing discrete deposits of charge of varying volume along a horizontal lateral cross section of said termination region.

16. (currently amended) The method of claim 14 wherein said steps (a) and (b) comprise doping in concentrations such that field strength along any horizontal lateral or vertical cross section is no greater than 15 volts per micrometer.